

## ABSTRACT OF THE DISCLOSURE

To provide a semiconductor laser device which is highly reliable even in high-power operation and has a long lifetime, and an optical disc unit using the semiconductor laser device. A semiconductor laser device having an oscillation wavelength of larger than 760 nm and smaller than 800 nm in which, on an n-type GaAs substrate (101), there are stacked in sequence an n-type first and second lower cladding layers (103, 104), a lower guide layer (105), a quantum well active layer (107), an upper guide layer (109) and a p-type upper cladding layer (110). The quantum well active layer (107) is composed of two InGaAsP compressively strained quantum well layers and three InGaAsP barrier layers alternately disposed in a manner such that an n-side barrier layer is present on a side of the lower guide layer (105) and that a p-side barrier layer is present on a side of the upper guide layer (109). The n-side barrier layer is set to have a thickness of 130 Å, which causes holes hard to tunnel. The p-side barrier layer is set to have a thickness of 50 Å, which facilitates tunneling of holes.